

Applications

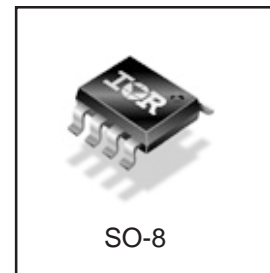
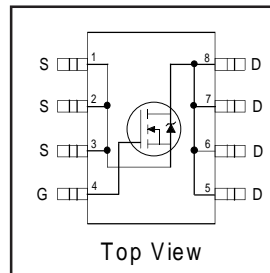
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use
- High Frequency Buck Converters for Computer Processor Power

HEXFET® Power MOSFET

V_{DSS}	R_{DS(on)} max	I_D
40V	13mΩ	10A

Benefits

- Ultra-Low Gate Impedance
- Very Low R_{DS(on)}
- Fully Characterized Avalanche Voltage and Current



Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V _{DS}	Drain-Source Voltage	40	V
V _{GS}	Gate-to-Source Voltage	± 20	V
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ 10V	10	A
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ 10V	8.3	
I _{DM}	Pulsed Drain Current ^①	83	
P _D @ T _A = 25°C	Maximum Power Dissipation ^③	2.5	W
P _D @ T _A = 70°C	Maximum Power Dissipation ^③	1.6	W
	Linear Derating Factor	0.02	mW/°C
T _J , T _{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
R _{θJL}	Junction-to-Drain Lead	—	20	°C/W
R _{θJA}	Junction-to-Ambient ^④	—	50	

Notes ① through ④ are on page 8
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IRF7471

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Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	40	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.043	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	9.5	13	mΩ	V _{GS} = 10V, I _D = 10A ③
		—	12	16		V _{GS} = 4.5V, I _D = 8.0A ③
V _{GS(th)}	Gate Threshold Voltage	1.0	—	3.0	V	V _{DS} = V _{GS} , I _D = 250μA
I _{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	V _{DS} = 32V, V _{GS} = 0V
		—	—	100		V _{DS} = 32V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	V _{GS} = 16V
	Gate-to-Source Reverse Leakage	—	—	-200		V _{GS} = -16V

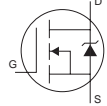
Dynamic @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g _{fs}	Forward Transconductance	22	—	—	S	V _{DS} = 20V, I _D = 8.0A
Q _g	Total Gate Charge	—	21	32	nC	I _D = 8.0A
Q _{gs}	Gate-to-Source Charge	—	7.2	11		V _{DS} = 20V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	8.2	12		V _{GS} = 4.5V ③
Q _{oss}	Output Gate Charge	—	23	35		V _{GS} = 0V, V _{DS} = 16V
t _{d(on)}	Turn-On Delay Time	—	12	—	ns	V _{DD} = 20V
t _r	Rise Time	—	2.7	—		I _D = 8.0A
t _{d(off)}	Turn-Off Delay Time	—	15	—		R _G = 1.8Ω
t _f	Fall Time	—	4.1	—		V _{GS} = 4.5V ③
C _{iss}	Input Capacitance	—	2820	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	700	—		V _{DS} = 20V
C _{rss}	Reverse Transfer Capacitance	—	46	—		f = 1.0MHz

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy②	—	300	mJ
I _{AR}	Avalanche Current①	—	8.0	A

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	2.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	83		
V _{SD}	Diode Forward Voltage	—	0.80	1.3	V	T _J = 25°C, I _S = 8.0A, V _{GS} = 0V ③
		—	0.65	—		T _J = 125°C, I _S = 8.0A, V _{GS} = 0V
t _{rr}	Reverse Recovery Time	—	69	100	ns	T _J = 25°C, I _F = 8.0A, V _R = 20V
Q _{rr}	Reverse Recovery Charge	—	130	200	nC	di/dt = 100A/μs ③
t _{rr}	Reverse Recovery Time	—	73	110	ns	T _J = 125°C, I _F = 8.0A, V _R = 20V
Q _{rr}	Reverse Recovery Charge	—	160	240	nC	di/dt = 100A/μs ③

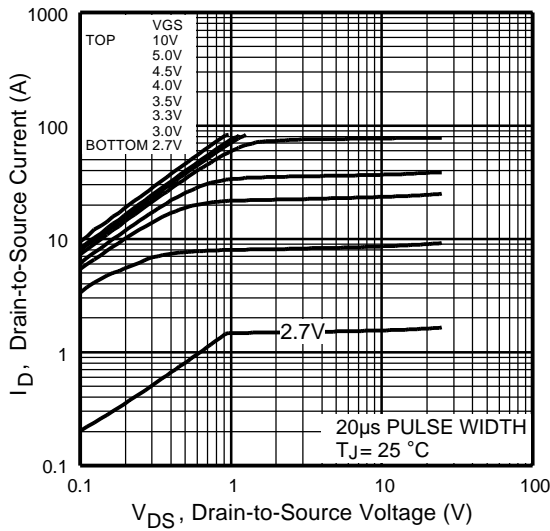


Fig 1. Typical Output Characteristics

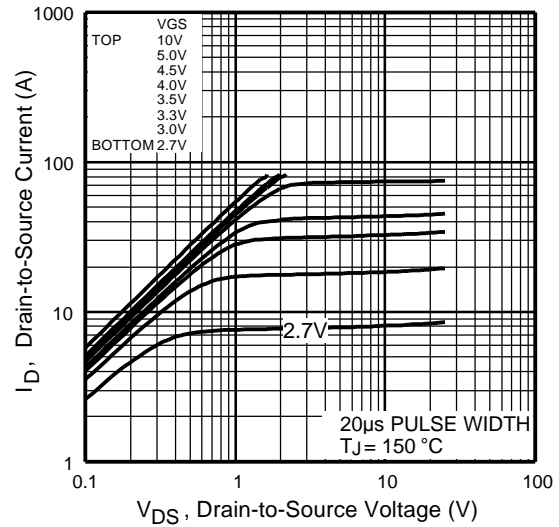


Fig 2. Typical Output Characteristics

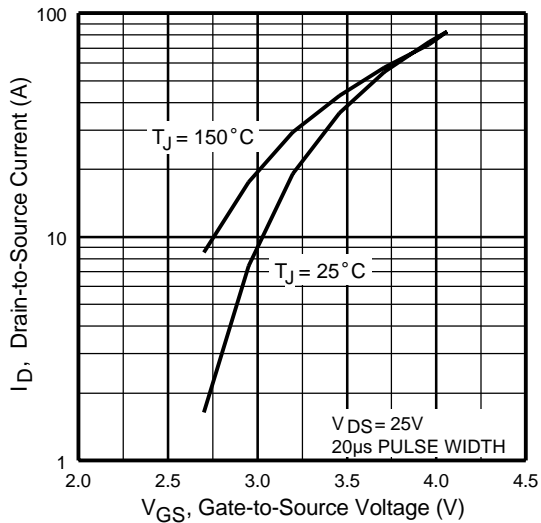


Fig 3. Typical Transfer Characteristics

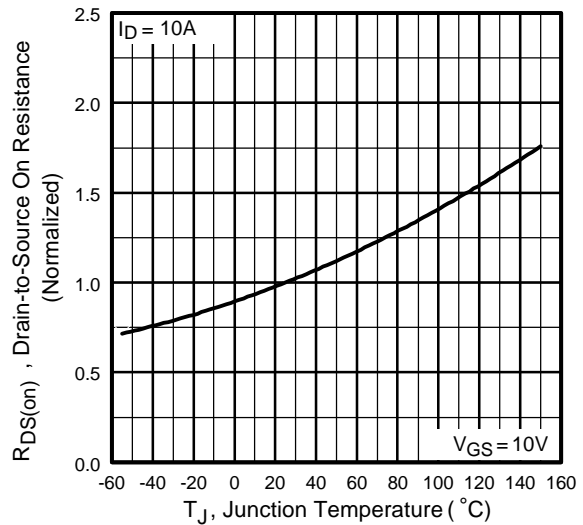


Fig 4. Normalized On-Resistance Vs. Temperature

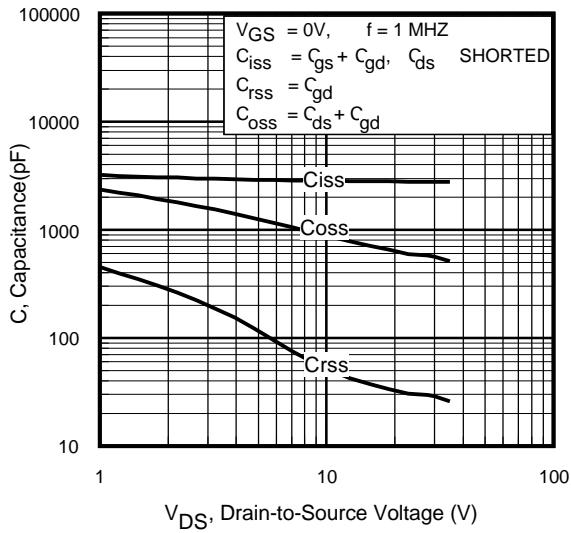


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

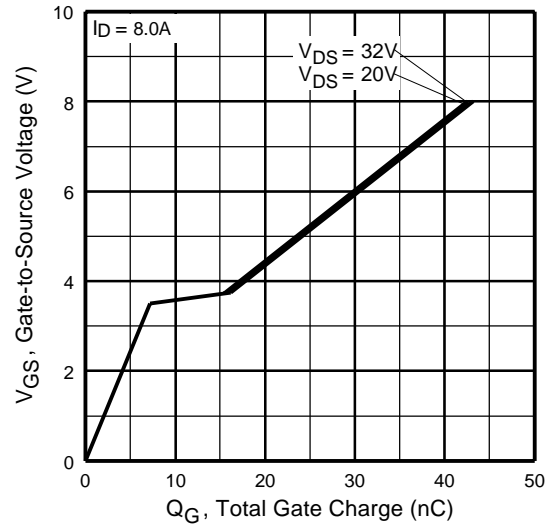


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

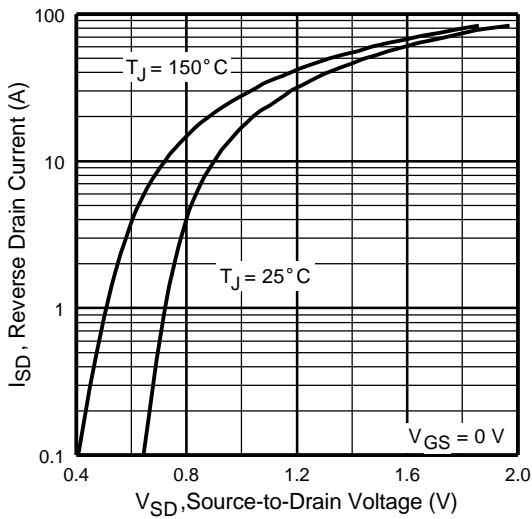


Fig 7. Typical Source-Drain Diode Forward Voltage

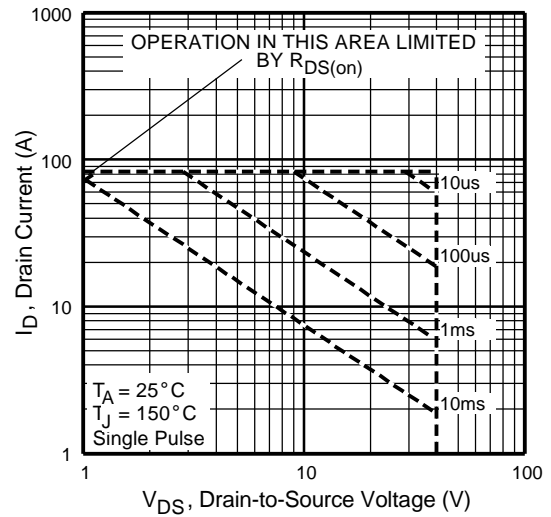


Fig 8. Maximum Safe Operating Area

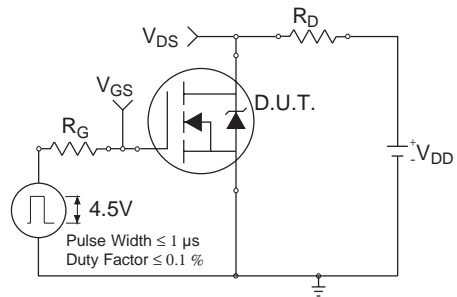
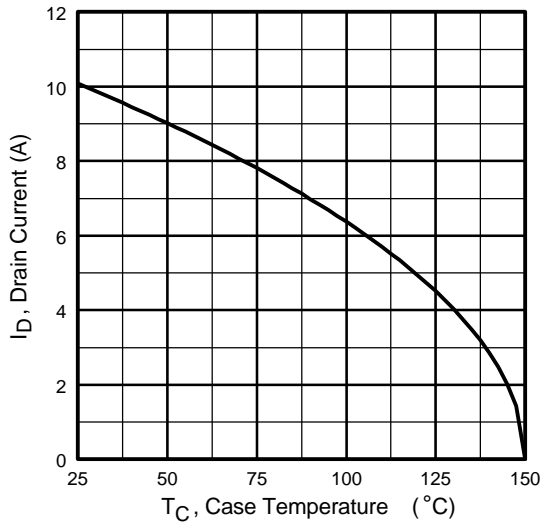


Fig 10a. Switching Time Test Circuit

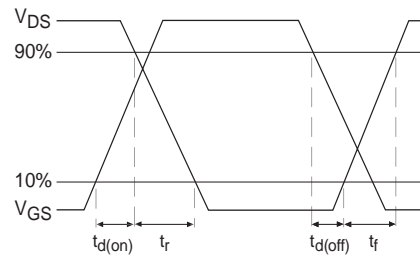


Fig 10b. Switching Time Waveforms

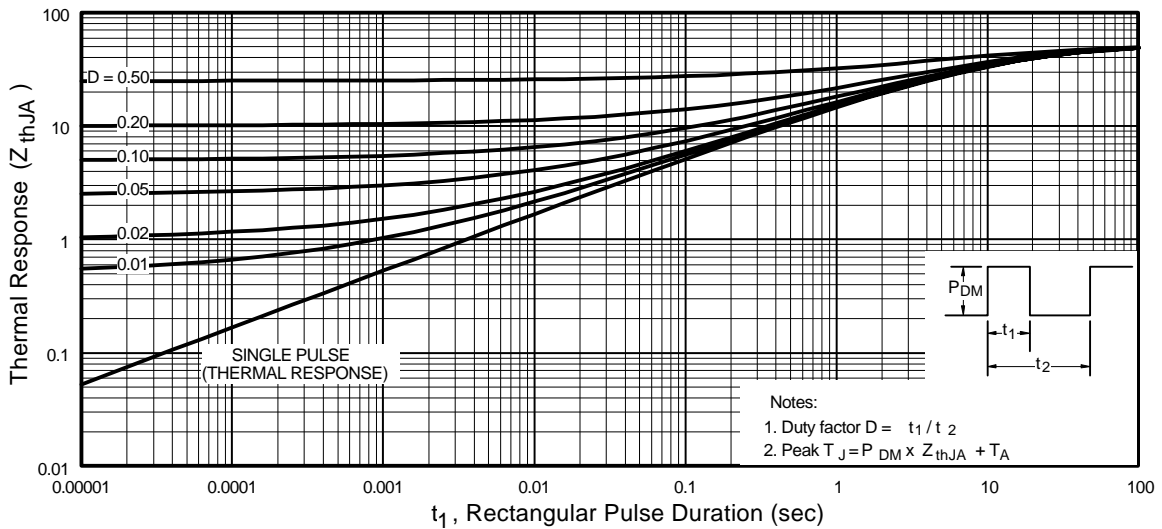


Fig 10. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

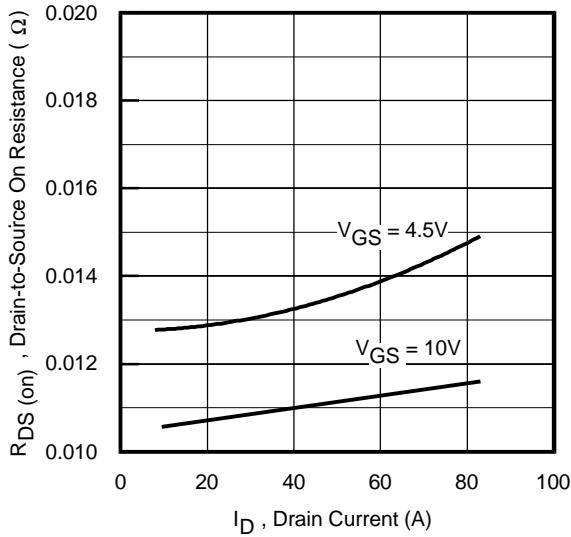


Fig 12. On-Resistance Vs. Drain Current

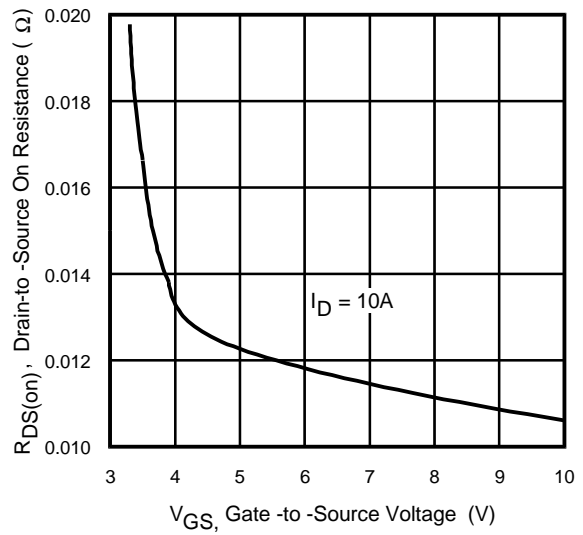


Fig 13. On-Resistance Vs. Gate Voltage



Fig 13a&b. Basic Gate Charge Test Circuit and Waveform

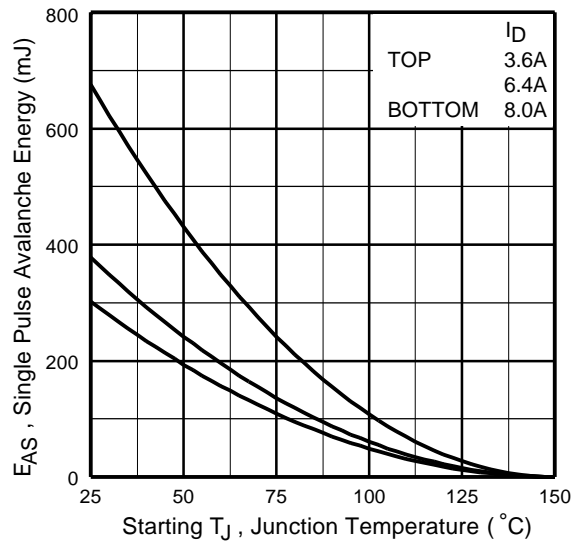


Fig 14c. Maximum Avalanche Energy Vs. Drain Current

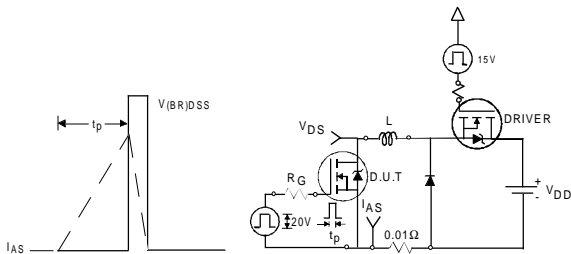
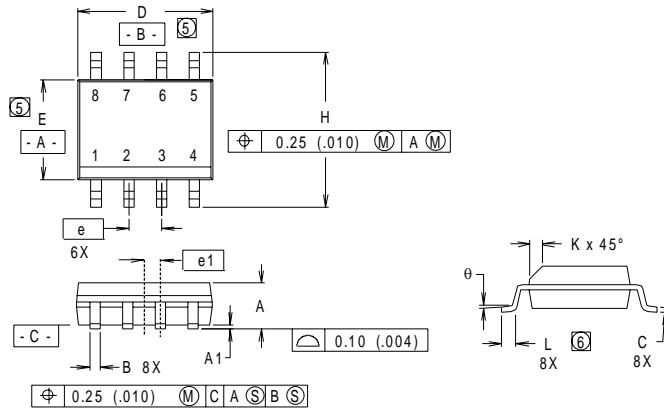


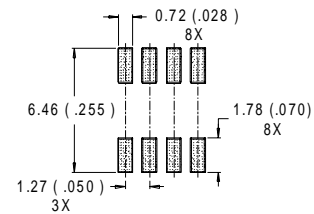
Fig 14a&b. Unclamped Inductive Test circuit and Waveforms

SO-8 Package Details



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
B	.014	.018	0.36	0.46
C	.0075	.0098	0.19	0.25
D	.189	.196	4.80	4.98
E	.150	.157	3.81	3.99
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.011	.019	0.28	0.48
L	0.16	.050	0.41	1.27
θ	0°	8°	0°	8°

RECOMMENDED FOOTPRINT

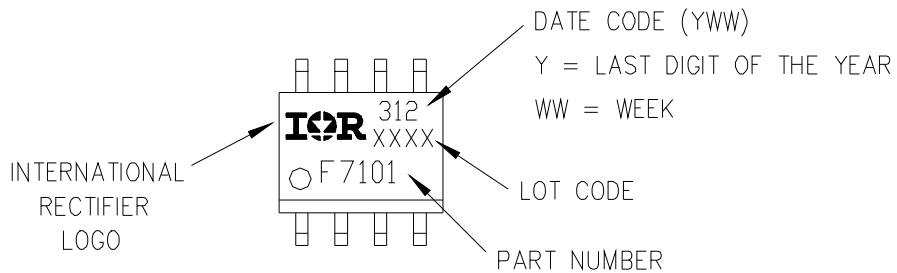


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION : INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS
MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.006).
- ⑥ DIMENSIONS IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE..

SO-8 Part Marking

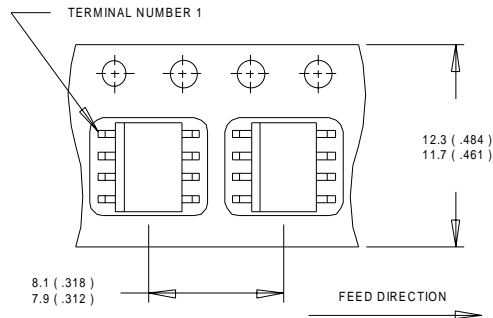
EXAMPLE: THIS IS AN IRF7101



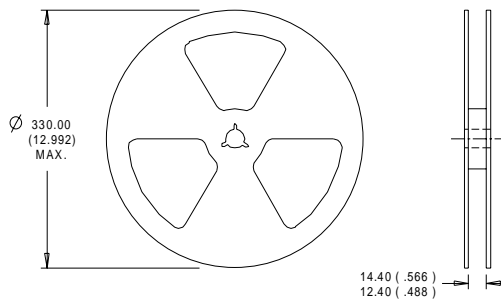
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SO-8 Tape and Reel



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 9.4\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 8.0\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board.

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IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
IR EUROPEAN REGIONAL CENTER: 439/445 Godstone Rd, Whyteleafe, Surrey CR3 OBL, UK Tel: ++ 44 (0)20 8645 8000
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Data and specifications subject to change without notice. 11/00